HiPerFRED™ Epitaxial Diode
dual diode, common cathode

MEK 600-04 DA

V_{RRM} = 400 V
I_{FAVM} = 880 A
t_{rr} = 220 ns

V_{RSM} V	V_{RRM} V	Type
400	400	MEK 600-04DA

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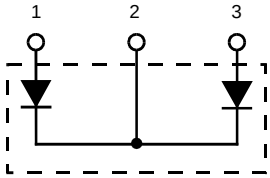
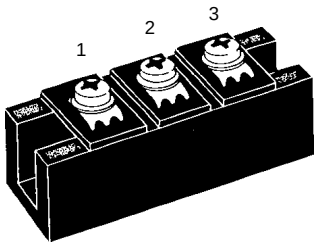




Symbol	Conditions	Maximum Ratings	
I_{FAVM}	T_C = 25°C; rectangular, d = 0.5	880	A
I_{FAVM}	T_C = 80°C; rectangular, d = 0.5	575	A
I_{FSM}	T_{VJ} = 25°C; t = 10 ms (50 Hz), sine	tbd	A
T_{VJ}		-40...+150	°C
T_{stg}		-40...+125	°C
P_{tot}	T_C = 25°C	1100	W
V_{ISOL}	50/60 Hz, RMS; $I_{ISOL} \leq$ 1 mA	3600	V~
M_d	Mounting torque with screw M5	2.25-2.75/20-25	Nm/lb.in.
	Terminal connection torque	4.5-5.5/40-48	Nm/lb.in.
a	Allowable acceleration	50	m/s^2

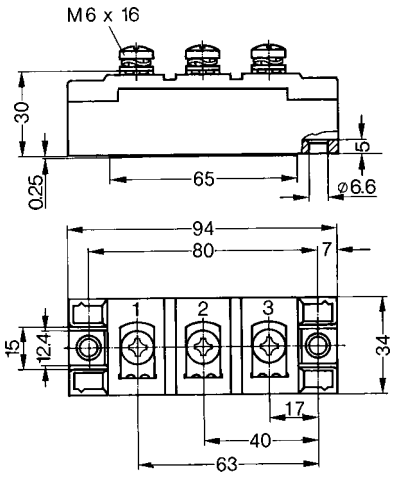
Symbol	Conditions	Characteristic Values min.	typ.	max.	
I_R	T_{VJ} = 25°C $V_R = V_{RRM}$			6	mA
	T_{VJ} = 125°C $V_R = V_{RRM}$		6		mA
V_F	I_F = 400 A; T_{VJ} = 125°C			1.1	V
	T_{VJ} = 25°C			1.4	V
t_{rr}	V_R = 100 V; $-di_F/dt$ = 900 A/µs		220		ns
I_{RM}	I_F = 400 A; T_{VJ} = 125°C		80		A
R_{thJS}				0.11	K/W
R_{thJC}				0.22	K/W
d_S	Creeping distance on surface	12.7			mm
d_A	Strike distance through air	9.6			mm
Weight			150		g

Data according to IEC 60747

Features
- HiPerFRED™ diode chips
  - fast reverse recovery
  - low operating forward voltage
  - low leakage current
  - avalanche capability
- Industry Standard package
  - with isolated DCB ceramic base plate
  - UL registered E72873

Applications
- Topologies
  - dual diode with common cathode
  - high current single diode with pins 1 and 3 paralleled
- Circuits
  - free wheeling diode of choppers, H-bridges, phaselegs etc.
  - secondary rectifier for switched mode power supplies, welders etc.

Dimensions in mm (1 mm = 0.0394")



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IXYS reserves the right to change limits, test conditions and dimensions.

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